

# HSK110

## Silicon Epitaxial Planar Diode for UHF/VHF tuner Band Switch

# HITACHI

Rev. 1  
Jun. 1994

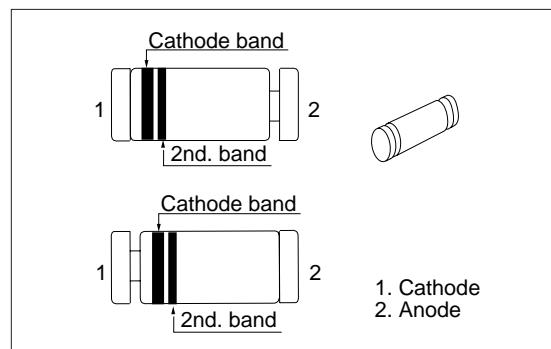
### Features

- Low forward resistance. ( $r_f = 0.9\Omega$  max)
- LLD package is suitable for high density surface mounting and high speed assembly.

### Ordering Information

Type No.	Cathode band	2nd.band	Package code
HSK110	White	Blue	LLD

### Outline



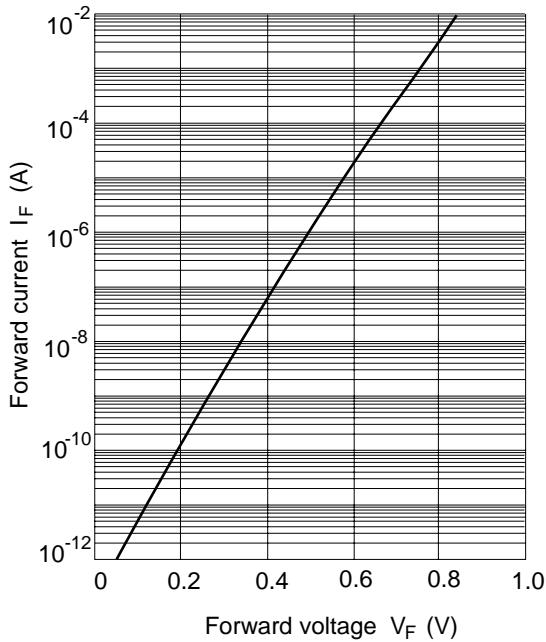
### Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

Item	Symbol	Value	Unit
Reverse voltage	$V_R$	35	V
Forward current	$I_F$	100	mA
Operation temperature	$T_{opr}$	-20 to + 60	°C
Storage temperature	$T_{stg}$	-55 to +125	°C

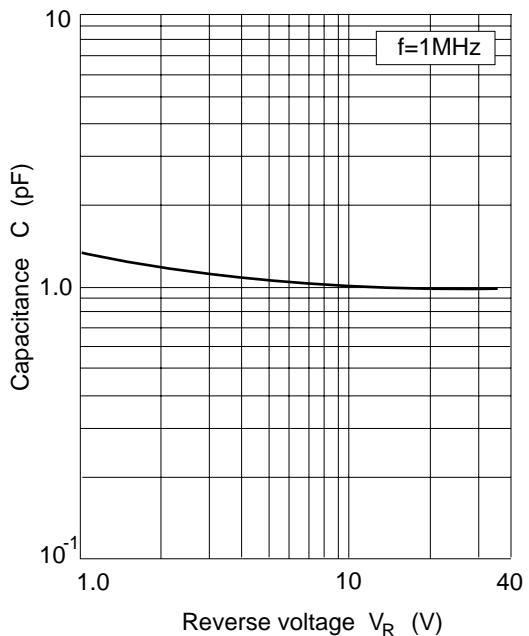
### Electrical Characteristics ( $T_a = 25^\circ C$ )

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	$V_F$	0.65	—	1.05	V	$I_F = 1 \text{ mA}$
Reverse voltage	$V_R$	35	—	—	V	$I_R = 1 \mu\text{A}$
Reverse current	$I_R$	—	—	0.1	$\mu\text{A}$	$V_R = 25 \text{ V}$
Capacitance	C	—	—	1.2	pF	$V_R = 6 \text{ V}, f = 1 \text{ MHz}$
Forward resistance	$r_f$	—	—	0.9	$\Omega$	$I_F = 2 \text{ mA}, f = 100 \text{ MHz}$

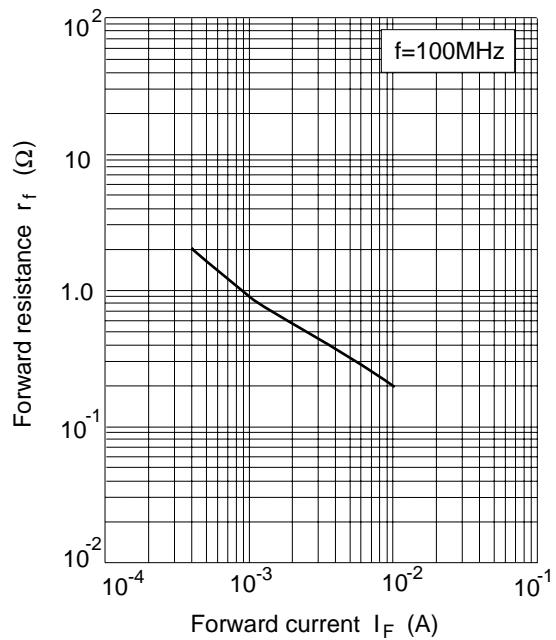
## HSK110



**Fig.1** Forward current Vs.  
Forward voltage



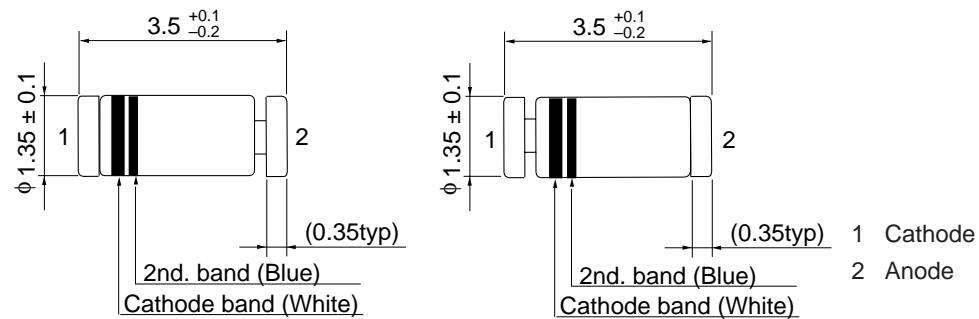
**Fig.2** Capacitance Vs.  
Reverse voltage



**Fig.3** Forward resistance  
Vs. Forward current

**Package Dimensions**

Unit: mm



( ) : Reference only

HITACHI Code	LLD
JEDEC Code	—
EIAJ Code	—
Weight (g)	0.027